TLE84110EL

Deca-Half-Bridge Driver IC

Automotive Power





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Deca-Half-Bridge Driver IC

TLE84110EL





1 Overview

Features

- 10 Half Bridge Power Outputs
- 3.3V / 5V compatible inputs with hysteresis
- · Independently Diagnosable Outputs
- 16-bit Standard SPI interface with daisy chain capability for control and diagnosis
- Open load diagnostics in ON-state for all outputs
- All outputs with overload and short circuit protection and diagnosis
- · Overtemperature prewarning and protection
- · Over- and Undervoltage lockout
- Cross-current protection
- Thermally enhanced exposed pad package
- Green Product (RoHS compliant)
- AEC Qualified



PG-SSOP-24-4

Description

The TLE84110EL is a protected Deca-Half-Bridge-Driver designed especially for automotive motion control applications such as Heating, Ventilation and Air Conditioning (HVAC) flap DC motor control. It is part of the MonolythIC family in Infineon's Smart Power Technology SPT® which combines bipolar and CMOS control circuitry with DMOS power devices.

The 10 half bridge drivers are designed to drive DC motor loads in sequential or parallel operation. Operation modes forward (cw), reverse (ccw), brake and high impedance are controlled from a 16-bit SPI interface. The diagnosis features such as short circuit, open load, power supply failure and overtemperature in combination with its low quiescent current makes this device attractive for automotive applications. The extremely small fine pitch exposed pad PG-SSOP-24-4 package in a SO -14 body provides good thermal performance and reduces PCB-board space and costs.

Table 1 Product Summary

| Operating Voltage | V_{S} | 7 18 V |
|--|----------------------------------|-----------|
| Logic Supply Voltage | V_{DD} | 3.0 5.5 V |
| Maximum Supply Voltage for Load Dump Protection | $V_{S(LD)}$ | 40 V |
| Minimum Overcurrent Threshold | $I_{\mathrm{SD1-10_MOTOR}}$ | 0.8 A |
| $\overline{\text{Maximum On-State Path Resistance at } T_{j} = 150^{\circ}\text{C}}$ | R _{DSON(total)_HSx+LSy} | 2 + 2 Ω |
| Typical Quiescent Current at T_j = 85°C | I _{S (off))} | 1 μΑ |
| Maximum SPI Access Frequency | $f_{\sf SCLK}$ | 5 MHz |

| Туре | Package | Marking |
|------------|--------------|------------|
| TLE84110EL | PG-SSOP-24-4 | TLE84110EL |

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Block Diagram

2 Block Diagram

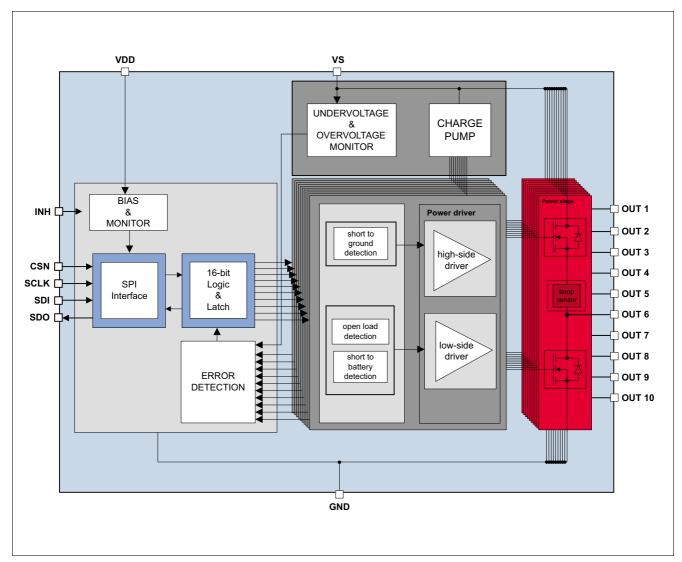


Figure 1 Block Diagram



Block Diagram

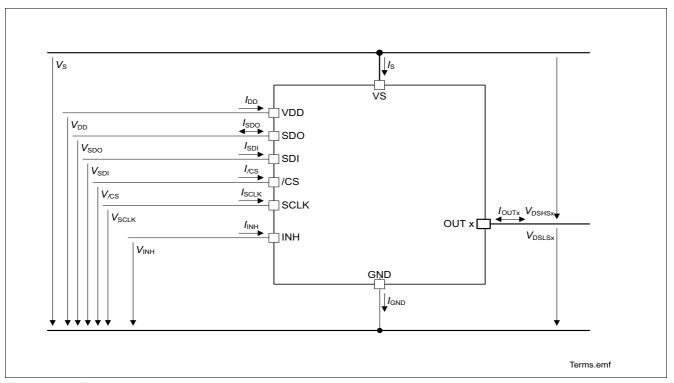


Figure 2 Terms



Pin Configuration

3 Pin Configuration

3.1 Pin Assignment

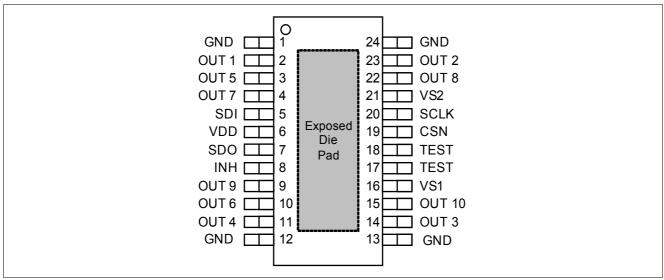


Figure 3 Pin Configuration



Pin Configuration

3.2 Pin Definitions and Functions

| Pin | Symbol | Function |
|-----|--------|--|
| 1 | GND | Ground |
| 2 | OUT 1 | Power Half-Bridge 1 |
| 3 | OUT 5 | Power Half-Bridge 5 |
| 4 | OUT 7 | Power Half-Bridge 7 |
| 5 | SDI | Serial-Data-Input |
| 6 | VDD | Logic Supply Voltage |
| 7 | SDO | Serial-Data-Output |
| 8 | INH | Inhibit input with internal pull-down; Place device in standby mode by pulling the INH line LOW |
| 9 | OUT 9 | Power Half-Bridge 9 |
| 10 | OUT 6 | Power Half-Bridge 6 |
| 11 | OUT 4 | Power Half-Bridge 4 |
| 12 | GND | Ground |
| 13 | GND | Ground |
| 14 | OUT 3 | Power Half-Bridge 3 |
| 15 | OUT 10 | Power Half-Bridge 10 |
| 16 | VS1 | Power Supply Voltage for Group 1 supplying current to OUT 3, OUT 4, OUT 6, OUT 9 and OUT 10. |
| 17 | TEST | Test input with internal pull down. Used for production test only. This pin should be left open or connected to ground on board. |
| 18 | TEST | Test input with internal pull down. Used for production test only. This pin should be left open or connected to ground on board. |
| 19 | CSN | Chip-Select-Not-Input |
| 20 | SCLK | Serial Clock Input |
| 21 | VS2 | Power Supply Voltage for Group 2 supplying current to OUT 1, OUT 2, OUT 5, OUT 7 and OUT 8. |
| 22 | OUT 8 | Power Half-Bridge 8 |
| 23 | OUT 2 | Power Half-Bridge 2 |
| 24 | GND | Ground |
| EDP | - | Exposed Die Pad; For cooling purposes only; Do not use as electrical ground.1) |
| | | |

¹⁾ The exposed die pad at the bottom of the package allows better heat dissipation from the device via the PCB. The exposed die pad is not connected to any active part of the IC. When connecting onto PCB, it can either be left floating or connected to GND for the best EMC and thermal performance.

Note: All GND pins must be externally connected together to a common GND potential. All VS pins must be externally connected together to a common Vs potential. See **Figure 17** for more Application Information.



4 General Product Characteristics

4.1 Absolute Maximum Ratings

Absolute Maximum Ratings 1)

 T_i = -40 °C to +150 °C

| Pos. | Parameter | Symbol | Limit Values | | Unit | Conditions | |
|---------|---|--|--------------|------|------|---|--|
| | | | Min. Max. | | | | |
| Voltage | s | | | | | | |
| 4.1.1 | Supply voltage | V_{S} | -0.3 | 40 | V | $V_{\rm S} = V_{\rm S1} = V_{\rm S2}$ | |
| 4.1.2 | Logic supply voltage | V_{DD} | -0.3 | 5.5 | V | 0 V < V _S < 40 V | |
| 4.1.3 | Logic input voltages (SDI, SCLK, CSN; INH) | $\begin{matrix} V_{\rm SDI}, V_{\rm SCLK}, \\ V_{\rm CSN}, V_{\rm INH} \end{matrix}$ | -0.3 | 5.5 | V | $0 \text{ V} < V_{\text{S}} < 40 \text{ V}$ $0 \text{ V} < V_{\text{DD}} < 5.5 \text{V}$ | |
| 4.1.4 | Logic output voltage (SDO) | V_{SDO} | -0.3 | 5.5 | V | 0 V < V _S < 40 V 0 V < V _{DD} < 5.5V | |
| Current | s | | | | | | |
| 4.1.5 | Continuous Supply Current for $V_{\rm S1}$ | I_{S1} | 0 | 2.50 | Α | _ | |
| 4.1.6 | Continuous Supply Current for $V_{\rm S2}$ | I_{S2} | 0 | 2.50 | Α | _ | |
| Temper | atures | | | | | | |
| 4.1.7 | Junction temperature | $T_{\rm j}$ | -40 | 150 | °C | _ | |
| 4.1.8 | Storage temperature | T_{stg} | -50 | 150 | °C | _ | |
| ESD Su | sceptibility | | • | | | | |
| 4.1.9 | ESD capability of OUTx and V_{S} pin | V_{ESD} | -4 | 4 | kV | 2) | |
| 4.1.10 | ESD capability of other pins | V_{ESD} | -2 | 2 | kV | 2) | |
| | | | | | | 1 | |

¹⁾ Not subject to production test, specified by design.

Note: Stresses above the ones listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Note: Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

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²⁾ Human Body Model according to ANSI EOS\ESD S5.1 standard (eqv. to MIL STD 883D and JEDEC JESD22-A114)



4.2 Functional Range

| Pos. | Parameter | Symbol | Lim | it Values | Unit | Conditions |
|-------|---|--|---------------------|---------------------|------|---|
| | | | Min. | Max. | | |
| 4.2.1 | Supply voltage range for normal operation | $V_{S(nor)}$ | 7 | 18 | V | _ |
| 4.2.2 | Extended Supply Voltage Range for Operation | $V_{S(ext)}$ | V _{UV OFF} | V _{OV OFF} | V | Limit Values Deviations Possible; After $V_{\rm S}$ rising above $V_{\rm UVON}$ |
| 4.2.3 | Supply Voltage Slew Rate | $ dV_s/dt $ | - | 10 | V/µs | $V_{\rm S}$ increasing and decreasing ¹⁾ |
| 4.2.4 | Logic supply voltage range for normal operation | V_{DD} | 3.0 | 5.5 | V | _ |
| 4.2.5 | Logic input voltages (DI, CLK, CSN; INH) | $V_{ m DI},V_{ m CLK},\ V_{ m CSN},V_{ m INH}$ | -0.3 | 5.5 | V | _ |
| 4.2.6 | Junction temperature | T_{j} | -40 | 150 | °C | _ |

¹⁾ Not subject to production test, specified by design.

Note: Within the functional range the IC operates as described in the circuit description. The electrical characteristics are specified within the conditions given in the related electrical characteristics table.

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4.3 Thermal Resistance

| Pos. | Parameter | Symbol | | Limit Val | ues | Unit | Conditions |
|--------|---|--------------------------------|------|-----------|------|------|------------|
| | | | Min. | Тур. | Max. | | |
| 4.3.1 | Junction to Case, Ta = -40°C | $R_{ m thjC_cold}$ | _ | 3 | _ | K/W | 1) |
| 4.3.2 | Junction to Case, Ta = 85°C | R_{thjC_hot} | _ | 4 | _ | K/W | 1) |
| 4.3.3 | Junction to Ambient, Ta = -40°C (1s0p, minimal footprint) | $R_{ m thjA_cold_min}$ | _ | 114 | _ | K/W | 1) 2) |
| 4.3.4 | Junction to Ambient, Ta = 85°C (1s0p, minimal footprint) | $R_{ m thjA_hot_min}$ | _ | 96 | _ | K/W | 1) 2) |
| 4.3.5 | Junction to Ambient, Ta = -40°C (1s0p, 300mm2 Cu) | $R_{ m thjA_cold_300}$ | - | 69 | _ | K/W | 1) 3) |
| 4.3.6 | Junction to Ambient, Ta = 85°C (1s0p, 300mm2 Cu) | $R_{\rm thjA_hot_300}$ | - | 56 | - | K/W | 1) 3) |
| 4.3.7 | Junction to Ambient, Ta = -40°C (1s0p, 600mm2 Cu) | $R_{\mathrm{thjA_cold_600}}$ | - | 62 | - | K/W | 1) 4) |
| 4.3.8 | Junction to Ambient, Ta = 85°C (1s0p, 600mm2 Cu) | $R_{ m thjA_hot_600}$ | _ | 50 | _ | K/W | 1) 4) |
| 4.3.9 | Junction to Ambient, Ta = -40°C (2s2p) | $R_{ m thjA_cold_2s2p}$ | _ | 35 | _ | K/W | 1) 5) |
| 4.3.10 | Junction to Ambient, Ta = 85°C (2s2p) | $R_{ m thjA_hot_2s2p}$ | _ | 30 | _ | K/W | 1) 5) |

- 1) Not subject to production test, specified by design.
- 2) Specified RthJA value is according to JEDEC JESD51-2,-3 at natural convection on FR4 1s0p board; The Product (Chip+Package) was simulated on a 76.2 x 114.3 x 1.5 mm board with minimal footprint copper area and 35 μm thickness. Ta = -40°C, Ch 1 to Ch 10 are dissipating a total of 1.8W (0.18W each).
- 3) Specified RthJA value is according to JEDEC JESD51-2,-3 at natural convection on FR4 1s0p board; The Product (Chip+Package) was simulated on a 76.2 x 114.3 x 1.5 mm board with additional cooling of 300 mm2 copper area and 35 µm thickness. Ta = -40°C, Ch 1 to Ch 10 are dissipating a total of 2.5W (0.25W each). Ta = 85°C, Ch 1 to Ch 10 are dissipating a total of 1.8W (0.18W each).
- 4) Specified RthJA value is according to JEDEC JESD51-2,-3 at natural convection on FR4 1s0p board; The Product (Chip+Package) was simulated on a 76.2 x 114.3 x 1.5 mm board with additional cooling of 600 mm2 copper area and 35 μm thickness. Ta = -40°C, Ch 1 to Ch 10 are dissipating a total of 2.5W (0.25W each). Ta = 85°C, Ch 1 to Ch 10 are dissipating a total of 1.8W (0.18W each).
- 5) Specified RthJA value is according to JEDEC JESD51-2,-3 at natural convection on FR4 2s2p board; The Product (Chip+Package) was simulated on a 76.2 x 114.3 x 1.5 mm board with 2 inner copper layers (4 x 35μm Cu). Ta = -40°C, Ch 1 to Ch 10 are dissipating a total of 2.5W (0.25W each). Ta = 85°C, Ch 1 to Ch 10 are dissipating a total of 1.8W (0.18W each).

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4.4 Electrical Characteristics

Electrical Characteristics

 $V_{\rm S}$ = 7 V to 18 V, $V_{\rm DD}$ = 3.0 V to 5.5 V, $T_{\rm j}$ = -40 °C to +150 °C, INH = HIGH; $I_{\rm OUT1-10}$ = 0 A; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

| Pos. | Parameter | Symbol | L | imit Val | ues | Unit | Conditions |
|----------|--------------------------------------|-------------------------------|------|----------|------|------|---|
| | | | Min. | Тур. | Max. | | |
| Curren | t Consumption, INH = GND | 1 | II. | | | | |
| 4.4.1 | Supply Quiescent current | I_{SQ} | _ | 1 | 2.5 | μА | $V_{\rm S}$ = 13.5 V; $V_{\rm DD}$ = 0 V $T_{\rm j}$ = 85°C |
| 4.4.2 | Logic supply quiescent current | $I_{DD_{Q}}$ | _ | 0.5 | 1 | μA | $T_{\rm i} = 85^{\circ}{\rm C}$ |
| 4.4.3 | Total quiescent current | $I_{SQ} + I_{DD_Q}$ | _ | 2 | 4 | μA | $T_{\rm i} = 85^{\circ}{\rm C}$ |
| Curren | t Consumption, INH = HIGH | | II. | | | | |
| 4.4.4 | Supply current | I_{S} | - | 4.5 | 10 | mA | Power drivers and power stages are of |
| 4.4.5 | Logic supply current | I_{DD} | _ | 1.5 | 3 | mA | SPI not active |
| 4.4.6 | Logic supply current | $I_{\mathrm{DD_RUN}}$ | _ | 5 | _ | mA | $V_{\rm DD}$ = 3.0V; SPI 5MHz |
| 4.4.7 | Total supply current | $I_{\rm S} + I_{\rm DD_RUN}$ | _ | 9.5 | _ | mA | _ |
| Over- a | nd Undervoltage Lockout | | | | - | | • |
| 4.4.8 | UV Switch ON voltage | V_{UVON} | _ | _ | 5.2 | V | $V_{\rm S}$ increasing |
| 4.4.9 | UV Switch OFF voltage | V_{UVOFF} | 4 | _ | 5.0 | V | $V_{\rm S}$ decreasing |
| 4.4.10 | UV ON/OFF hysteresis | V_{UVHY} | _ | 0.25 | _ | V | V _{UV ON} - V _{UV OFF} |
| 4.4.11 | OV Switch OFF voltage | V_{OVOFF} | 21 | _ | 25 | V | $V_{\rm S}$ increasing; |
| 4.4.12 | OV Switch ON voltage | V_{OVON} | 20 | _ | 24 | V | $V_{\rm S}$ decreasing; |
| 4.4.13 | OV ON/OFF hysteresis | V_{OVHY} | _ | 1 | _ | V | $V_{\text{OV OFF}}$ - $V_{\text{OV ON}}$; |
| 4.4.14 | V _{DD} Power-On-Reset | $V_{DD\;POR}$ | 2.60 | 2.80 | 3.00 | V | V_{DD} increasing |
| 4.4.15 | V _{DD} Power-Off-Reset | $V_{ m DD~POffR}$ | 2.50 | 2.70 | 2.90 | V | V_{DD} decreasing |
| Static [| Drain-source ON-Resistance | | | | · | | |
| 4.4.16 | High- and Low-side switch | R _{DSON(1-10)} | _ | 0.8 | _ | Ω | $I_{OUT (1-10)}$ = ±0.5 A; T_{j} = 25 °C |
| | | | _ | 1.4 | 2 | Ω | $I_{OUT (1-10)}$ = ±0.5 A; T_{j} = 150 °C |
| Output | Protection and Diagnosis | | | | | | |
| High-Si | ide Switches | | | | | | |
| 4.4.17 | HS Overcurrent Shutdown Threshold | I_{SD_HS} | -1.6 | -1.15 | -0.8 | A | HS Switch; $V_{\rm S}$ =13.5V; See Figure 7 |
| 4.4.18 | HS Short Circuit Current Limit | I_{SC_HS} | -2.0 | -1.5 | -1.0 | Α | 1) |
| 4.4.19 | HS_Shutdown Delay Time | $t_{\sf dSD}$ | 10 | 25 | 50 | μs | HS Switch; $V_{\rm S}$ =13.5V; See Figure 7 |

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Electrical Characteristics (cont'd)

 $V_{\rm S}$ = 7 V to 18 V, $V_{\rm DD}$ = 3.0 V to 5.5 V, $T_{\rm j}$ = -40 °C to +150 °C, INH = HIGH; $I_{\rm OUT1-10}$ = 0 A; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

| Pos. | Parameter | Symbol | L | imit Val | ues | Unit | Conditions |
|----------|---|-------------------|------|----------|------|-----------------|---|
| | | | Min. | Тур. | Max. | | |
| Low-Sid | de Switches | • | ı | 1 | | • | |
| 4.4.20 | LS Overcurrent Shutdown Threshold | I_{SD_LS} | 8.0 | 1.15 | 1.6 | A | LS Switch; $V_{\rm S}$ =13.5V; See Figure 7 |
| 4.4.21 | LS Short Circuit Current Limit | I_{SC_LS} | 1.0 | 1.5 | 2.0 | А | 1) |
| 4.4.22 | LS_Shutdown Delay Time | $t_{\sf dSD}$ | 10 | 25 | 50 | μs | LS Switch; $V_{\rm S}$ =13.5V; See Figure 7 |
| 4.4.23 | Open Load Detection Current | I_{OLD} | 3 | 8 | 15 | mA | LS Switch; |
| 4.4.24 | Open Load Delay Time | $t_{\sf dOLD}$ | 200 | 350 | 600 | μs | $V_{\rm S}$ =13.5V; See Figure 8 |
| Output | Switching Times | | | | | | |
| 4.4.25 | High-Side ON delay-time | $t_{\sf dONH}$ | _ | 7.5 | 12 | μs | $V_{\rm S}$ =13.5V, resistive |
| 4.4.26 | High-Side OFF delay-time | t_{dOFFH} | _ | 3 | 6 | μs | Load = 100Ω , See |
| 4.4.27 | Low-Side ON delay-time | t_{dONL} | _ | 6.5 | 12 | μs | Figure 9 and Figure 10 |
| 4.4.28 | Low-Side OFF delay-time | t_{dOFFL} | _ | 2 | 5 | μs | rigule 10 |
| 4.4.29 | Dead Time H to L | t_{DHL} | 1.5 | _ | _ | μs | |
| 4.4.30 | Dead Time L to H | t_{DLH} | 2.5 | _ | _ | μs | |
| 4.4.31 | High-Side RiseTime | t_{ONH} | _ | 4 | _ | μs | |
| 4.4.32 | High-Side Fall Time | t_{OFFH} | _ | 2 | _ | μs | |
| 4.4.33 | Low-Side RiseTime | t_{OFFL} | _ | 1 | _ | μs | |
| 4.4.34 | Low-Side Fall Time | t_{ONL} | _ | 1 | _ | μs | |
| Input In | terface, Logic Inputs INH | | | | | | |
| 4.4.35 | High-input voltage | V_{INHH} | 70 | _ | _ | $\%~V_{ m DD}$ | _ |
| 4.4.36 | Low-input voltage | V_{INHL} | _ | _ | 30 | $\%~V_{ m DD}$ | _ |
| 4.4.37 | Hysteresis of input voltage | V_{INHHY} | 50 | 200 | 500 | mV | _ |
| 4.4.38 | Pull down resistor | R_{PD_INH} | _ | 120 | _ | kΩ | _ |
| SPI INT | TERFACE | | | | · | | |
| Delay T | ime from Sleep mode to first Data i | n | | | | | |
| 4.4.39 | Setup time | t_{set} | _ | _ | 100 | μs | 1) |
| 4.4.40 | Time between two consecutive SRR commands | t_{SRR} | 100 | _ | _ | μs | 1) |
| Input In | terface, Logic Inputs SDI, SCLK, C | SN | • | • | | • | |
| 4.4.41 | High-input voltage | V_{IH} | 70 | _ | _ | $\%~V_{DD}$ | _ |
| 4.4.42 | Low-input voltage | V_{IL} | _ | _ | 30 | $\%~V_{\rm DD}$ | _ |
| 4.4.43 | Hysteresis of input voltage | V_{IHY} | 50 | 200 | 500 | mV | _ |
| 4.4.44 | Pull up resistor at pin CSN | $R_{\sf PU_CSN}$ | _ | 140 | _ | kΩ | _ |
| 4.4.45 | Pull down resistor at pin SDI, SCLK | | - | 120 | - | kΩ | _ |

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Electrical Characteristics (cont'd)

 $V_{\rm S}$ = 7 V to 18 V, $V_{\rm DD}$ = 3.0 V to 5.5 V, $T_{\rm j}$ = -40 °C to +150 °C, INH = HIGH; $I_{\rm OUT1-10}$ = 0 A; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

| Pos. | Parameter | Symbol | L | imit Val | ues | Unit | Conditions | |
|----------|--|----------------------|-----------------------|-----------------------|--------|----------|--|--|
| | | | Min. | Тур. | Max. | | | |
| 4.4.46 | Input capacitance at pin CSN, SDI or SCLK | C_{I} | - 10 | 10 | 15 | pF | $0V < V_{DD} < 5.25V^{1)}$ | |
| Input In | terface, Logic Outputs SDO | | | | | | | |
| 4.4.47 | High-output voltage | V_{SDOH} | V _{DD} - 1.0 | V _{DD} - 0.7 | _ | V | $I_{\rm SDOH}$ = -1 mA | |
| 4.4.48 | Low-output voltage | V_{SDOL} | _ | 0.2 | 0.4 | V | I_{SDOL} = 1.6 mA | |
| 4.4.49 | Tri-state Leakage Current | I_{SDOLK} | -10 | _ | 10 | μΑ | $\begin{aligned} V_{\mathrm{CSN}} &= V_{\mathrm{DD}} \\ \mathrm{OV} &< V_{\mathrm{SDO}} < V_{\mathrm{DD}} \end{aligned}$ | |
| Data In | put Timing. See Figure 12 and Figu | re 15 | | - | - | | | |
| 4.4.50 | SCLK Frequency | f_{CLK} | _ | _ | 5 | MHz | 1) | |
| 4.4.51 | SCLK Period | t_{pCLK} | 500 200 | _ _ | _ _ | ns ns | $V_{\rm DD}$ = 5.25V $V_{\rm DD}$ = 3.0V ¹⁾ | |
| 4.4.52 | SCLK High Time | t_{SCLKH} | 85 | _ | _ | ns | 1) | |
| 4.4.53 | SCLK Low Time | t_{SCLKL} | 85 | _ | _ | ns | 1) | |
| 4.4.54 | SCLK Setup Time | t_{lag} | 85 | _ | _ | ns | 1) | |
| 4.4.55 | SDI Setup Time | $t_{\rm SDI_setup}$ | 50 | _ | _ | ns | 1) | |
| 4.4.56 | SDI Hold Time | $t_{\rm SDI_hold}$ | 50 | _ | _ | ns | 1) | |
| 4.4.57 | CSN Setup Time | t_{lead} | 100 | _ | _ | ns | 1) | |
| 4.4.58 | CSN High Time | t_{CSNH} | 500 | _ | _ | ns | 1) 2) | |
| 4.4.59 | Input Signal Rise Time at pin SDI, SCLK, CSN | $t_{\sf rIN}$ | _ | _ | 50 | ns | 1) | |
| 4.4.60 | Input Signal Fall Time at pin SDI, SCLK, CSN | t_{fIN} | - | _ | 50 | ns | 1) | |
| Data O | utput Timing. See Figure 14 and Fig | jure 15 | | " | " | | | |
| 4.4.61 | SDO Rise Time | t_{rSDO} | _ | 10 | 25 | ns | $C_{load} = 40pF^{-1}$ | |
| 4.4.62 | SDO Fall Time | t_{fSDO} | _ | 10 | 25 | ns | $C_{load} = 40pF^{-1}$ | |
| 4.4.63 | SDO Valid Time | $t_{\sf VASDO}$ | _ | 20 | 50 | ns | $V_{\rm SDO} < 0.2 V_{\rm DD} \ V_{\rm SDO} > 0.7 V_{\rm DD} \ {\rm C_{load}} = 40 {\rm pF}^{-1}$ | |
| 4.4.64 | SDO Enable Time after CSN falling edge | $t_{\sf ENSDO}$ | - | - | 50 | ns | Low Impedance 1) | |
| 4.4.65 | SDO Disable Time after CSN rising edge | $t_{\sf DISSDO}$ | - | - | 50 | ns | High Impedance 1) | |
| 4.4.66 | Duty cycle of incoming clock at SCLK | duty _{SCLK} | 40 | - | 60 | % | 1) | |



Electrical Characteristics (cont'd)

 $V_{\rm S}$ = 7 V to 18 V, $V_{\rm DD}$ = 3.0 V to 5.5 V, $T_{\rm j}$ = -40 °C to +150 °C, INH = HIGH; $I_{\rm OUT1-10}$ = 0 A; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

| Pos. | Parameter | Symbol | L | imit Val | ues | Unit | Conditions |
|--------|---|--------------------------|------|----------|------|----------|-----------------|
| | | | Min. | Тур. | Max. | | |
| Therma | al Prewarning & Shutdown | | | | | <u>'</u> | |
| 4.4.67 | Thermal warning junction temperature | T_{jW_enter} | 120 | 140 | 170 | °C | See Figure 6 1) |
| 4.4.68 | Thermal warning junction temperature - switch off | T_{jW_exit} | 90 | _ | 140 | °C | |
| 4.4.69 | Temperature warning hysteresis | ΔT_{iW} | _ | 30 | _ | K | |
| 4.4.70 | Thermal shutdown junction temperature | T_{jSD} | 150 | 175 | 200 | °C | |
| 4.4.71 | Thermal switch-on junction temperature | T_{jSO} | 130 | _ | 180 | °C | |
| 4.4.72 | Temperature shutdown hysteresis | ΔT_{jSD} | _ | 20 | _ | K | |
| 4.4.73 | Ratio of SD to W temperature | $T_{\rm iSD}/T_{\rm iW}$ | 1.05 | 1.20 | _ | _ | |

¹⁾ Not subject to production test, specified by design

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²⁾ CSN High Time: This is the minimum time the user must wait between SPI commands



5 Block Description

5.1 General

5.2 Power Supply

5.2.1 General

The TLE84110EL has two power supply inputs: The half bridge outputs are connected to $V_{\rm S}$ supply, which is connected to the 12V automotive supply rail. The internal logic part is supplied by a separate voltage $V_{\rm DD}$ = 5 V. $V_{\rm S}$ and $V_{\rm DD}$ supplies are separated so that information stored in the logic block remains intact in the event of voltage drop outs or disturbances on $V_{\rm S}$. The system can therefore continue to operate once $V_{\rm S}$ has recovered, without having to resend commands to the device.

A rising edge on $V_{\rm DD}$ triggers an internal Power-On Reset (POR) to initialize the IC at power-on. All data stored internally is deleted, and the outputs are switched to high-impedance status (tristate). A 10 μ F electrolytic and 100nF ceramic capacitor are recommended to be placed as close as possible to the $V_{\rm S}$ supply pin of the device for improved EMC performance in the high and low frequency band.

5.2.2 Sleep Mode

The TLE84110EL enters low power mode (or sleep mode) by setting the INH input to low. The INH input has an internal pull-down resistor. In sleep-mode, all output transistors are turned off and the SPI register banks are reset.

5.2.3 Reverse Polarity Protection

The TLE84110EL requires an external reverse polarity protection. During reverse polarity, the freewheeling diodes across the half bridge output will begin to conduct, causing an undesired current flow (I_{RB}) from ground potential to battery and excessive power dissipation across the diodes. As such, a reverse polarity protection diode is recommended (see **Figure 4**).

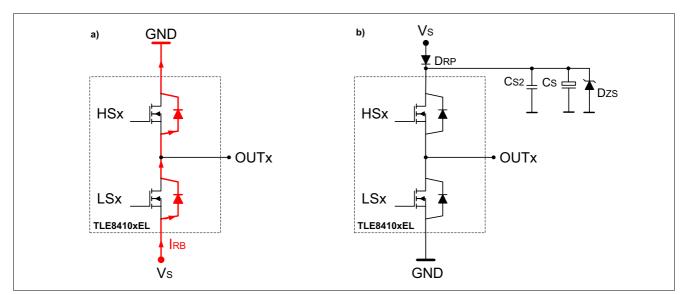


Figure 4 Reverse Polarity Protection

5.2.4 Power Supply Monitoring

The power supply rails $V_{\rm S}$ and $V_{\rm DD}$ are monitored for over- and undervoltage. See **Figure 5**.

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5.2.4.1 $V_{\rm S}$ Undervoltage

If the supply voltage $V_{\rm S}$ drops below the switch off voltage $V_{\rm UVOFF}$, all output transistors are switched off but logic information remains intact and uncorrupted. The "undervoltage" (Power Supply Fail, PSF) error bit is flagged and can be read out via SPI. Once $V_{\rm S}$ rises again and reaches the threshold switch on voltage $V_{\rm UVON}$, the power stages are restarted and the PSF error bit is reset.

5.2.4.2 $V_{\rm S}$ Overvoltage

If the supply voltage $V_{\rm S}$ rises above the switch off voltage $V_{\rm OVOFF}$, all output transistors are switched off and the "overvoltage" (PSF) error bit is set. The error is not latched, i.e. if $V_{\rm S}$ falls again and reaches the switch on voltage $V_{\rm OVON}$, the power stages are restarted and the Error Flags are reset.

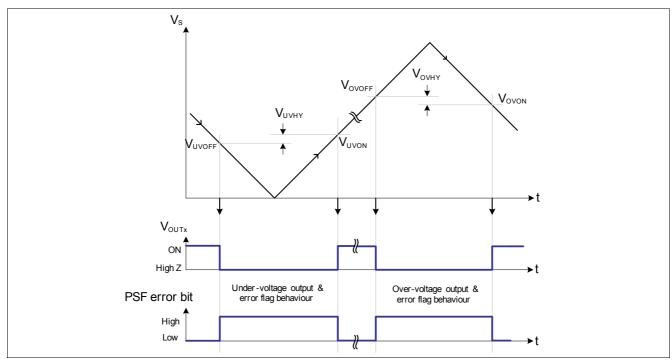


Figure 5 Output behavior during Over- and Undervoltage V_S condition

5.2.5 Reset Behavior

The following reset triggers have been implemented in the TLE84110EL:-

$V_{\rm DD}$ Undervoltage Reset:

The SPI Interface shall not function if $V_{\rm DD}$ is below the undervoltage threshold, $V_{\rm DD\,POffR}$. The digital Block will be initialized. The output stages are switched off to High-Z. The undervoltage reset and SRR is released once $V_{\rm DD}$ voltage levels are above the undervoltage threshold, $V_{\rm DD\,POR}$.

Reset on INH pin:

If the INH pin level is low, the device shall enter reset and the current consumption is reduced to $I_{SQ} + I_{DD_Q}$.

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5.3 Temperature Monitoring

Temperature sensors are integrated in the power stages. The temperature monitoring circuit compares the measured temperature to the warning and shutdown thresholds. If one or more temperature sensors reach the warning temperature, the temperature warning bit, TW is set to HIGH. This bit is not latched (i.e. if the temperature falls below the warning threshold (with hysteresis), the TW bit is reset to LOW again).

If one or more temperature sensors reach the shut-down temperature threshold, all outputs are shut down and latched (i.e. the output stages remain off until an SRR command is sent or a power-on reset is performed). See **Figure 6**.

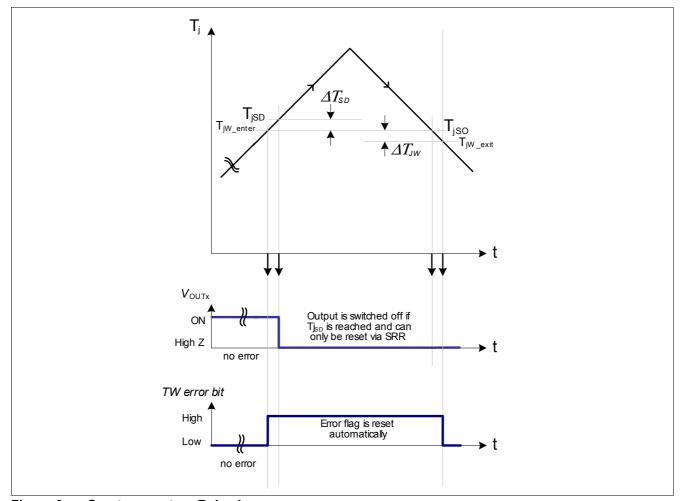


Figure 6 Overtemperature Behavior

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5.4 Protection and Diagnosis

This device features embedded protective functions which are designed to prevent IC destruction under fault conditions described in the following sections. Fault conditions are treated as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

5.4.1 Short Circuit of Output to Supply or Ground

The high-side switches are protected against short to ground where as the low-side switches are protected against short to supply.

If a switch is turned on and the current rises above the overcurrent shutdown threshold, $I_{\rm SD}$ for longer than the shutdown delay time $t_{\rm dSD}$, the output transistor is turned off and the corresponding diagnosis bit, OC, is set. During this delay time, the current is limited to $I_{\rm SC}$ as shown in **Figure 7**. The output stage remains off and the error bit remains set until a status register reset is sent to the SPI or a power-on reset is performed.

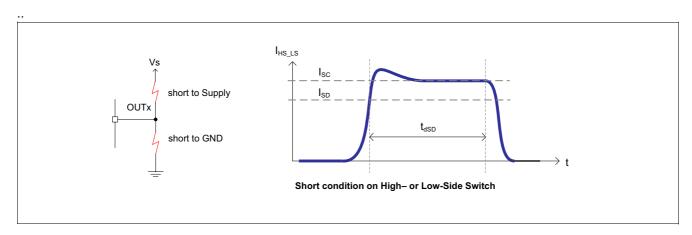


Figure 7 High-Side and Low-Side Switch - Short Circuit and Overcurrent Protection

5.4.2 Open Load

Open-load detection in ON-state is implemented in the Low-Side switches of the bridge outputs: If the current through the low side transistor is lower than the reference current $I_{\rm OLD}$ in ON-state for longer than the open-load detection delay time $t_{\rm dOLD}$, the corresponding open-load, OL diagnosis bit is set. The output transistor, however, remains ON. The open load error bit is latched and can be reset by the SPI status register reset or by a power-on reset.

As an example, if a motor is connected between outputs OUT 1 and OUT 2 with a broken wire as shown in Figure 8, the resulting diagnostic information is shown in Table 2.

Open Load Detection Shutdown (OL SD EN) Bit via the Control Register can be activated or deactivated as required. If the OL SD EN bit is set and an open load on the Low-Side Switch is detected, the respective output is disabled. The error remains latched and output is off until an SRR or power on reset is performed. This has the added advantage of independently diagnosing and isolating error flags to the corresponding failed output.

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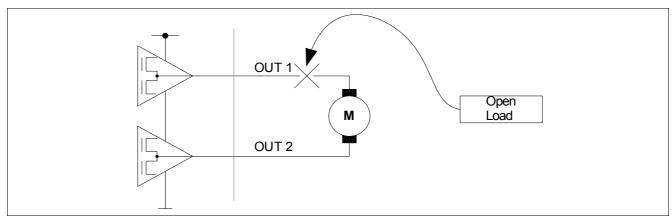


Figure 8 Open Load Example

Table 2 Open Load Diagnosis Example

| Control | | | | | Diagnostic Information | | | | | | | |
|-----------|-----------|---------------|-----------|--------------------|------------------------|---------------------------------------|------------|------------|--------------|--|--|--|
| | | Motor Conn | | | | Open Load Detection (OPLD) Error Flag | | | | | | |
| LS1 ON | HS1 ON | LS2 ON | HS2 ON | Motor Rotation | LS1 OpL | LS2 OpL | LS1 OpL | LS2 OpL | | | | |
| 0 | 0 | 0 | 0 | motor off | 0 | 0 | 0 | 0 | de-activated | | | |
| 1 | 0 | 0 | 1 | clock-wise | 0 | 0 | 1 | 0 | activated | | | |
| 0 | 1 | 1 | 0 | counter clock-wise | 0 | 0 | 0 | 1 | activated | | | |
| 0 | 1 | 0 | 1 | brake high | 0 | 0 | 0 | 0 | de-activated | | | |
| 1 | 0 | 1 | 0 | brake low | 1 | 1 | 1 | 1 | activated | | | |

5.4.3 Cross-Current

In bridge configurations the high-side and low-side power transistors are ensured never to be simultaneously "ON" to avoid cross currents. This is realized by integrating delays in the driver stage of the power outputs, intended to create a dead-time between switching off one Power Transistor and switching on of the other Power Transistor of the same half-bridge. To ensure that there is no overlap of the switching slopes that would lead to a cross current, the dead-times, $t_{\rm DHL}$ and $t_{\rm DLH}$ are specified.

In the event a cross-current has occurred, the device shall turn off both switches and the Overcurrent bit is set High.



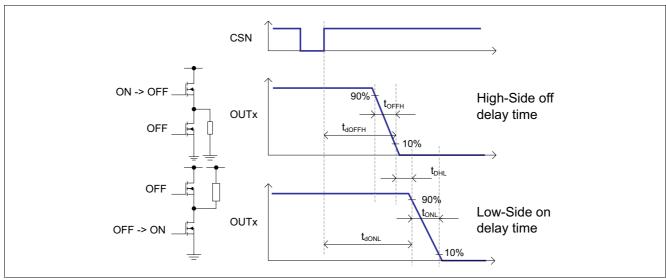


Figure 9 Timing Bridge Outputs High to Low

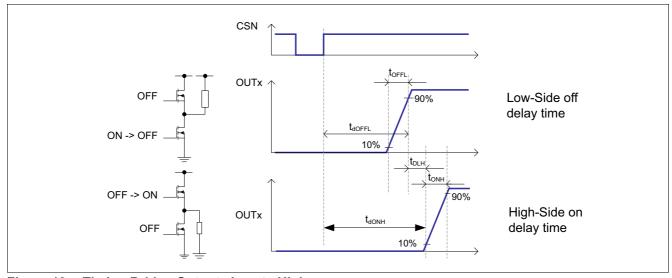


Figure 10 Timing Bridge Outputs Low to High





6.1 General

Infineon

The SPI is used for bidirectional communication with a control unit. The TLE84110EL acts as SPI-slave and the control unit acts as SPI-master. The 16-bit control word is read via the SDI serial data input. The status word appears synchronously at the SDO serial data output. The communication is synchronized by the serial clock input SCLK.

Standard data transfer timing is shown in **Figure 11**. The clock polarity is data valid on falling edge. SCLK must be low during CSN transition. The transfer is MSB first.

The transmission cycle begins when the chip is selected with the chip-select-not (CSN) input (H to L). Then the data is clocked through the shift register. The transmission ends when the CSN input changes from L to H and the word which has been read into the shift register becomes the control word. The SDO output switches then to tristate status, thereby releasing the SDO bus circuit for other uses. The SPI allows to parallel multiple SPI devices by using multiple CSN lines. The SPI can also be used with other SPI-devices in a daisy-chain configuration.

The control word transmitted from the master to the TLE84110EL is executed at the end of the SPI transmission ($CSN\ L\ ->\ H\)$ and remains valid until a different control word is transmitted or a power on reset occurs. At the beginning of the SPI transmission ($CSN\ H\ ->\ L\)$, the diagnostic data currently valid are latched into the SPI and transferred to the master.

Data integrity is maintained by polling multiples of 8 data bits to ensure that a valid command has been received.

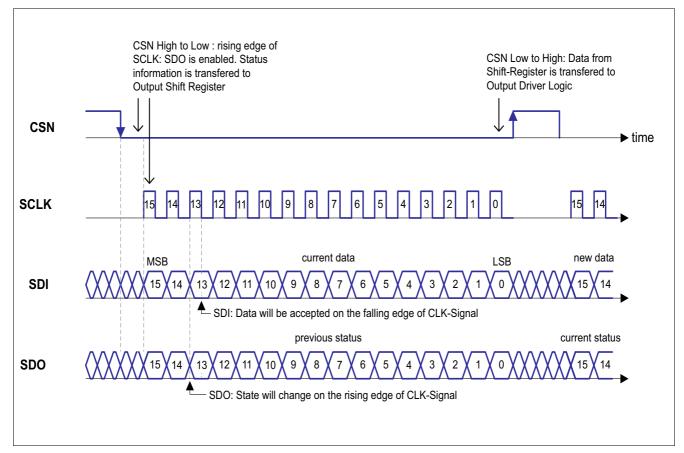


Figure 11 SPI Data Transfer Protocol

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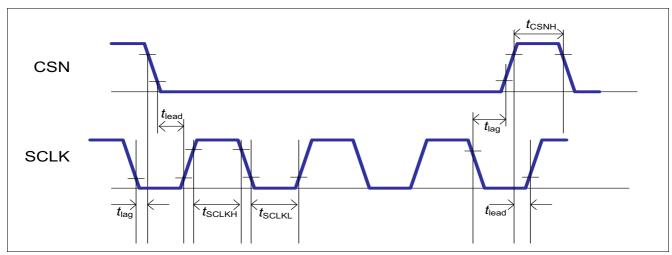


Figure 12 SPI SCLK and CSN

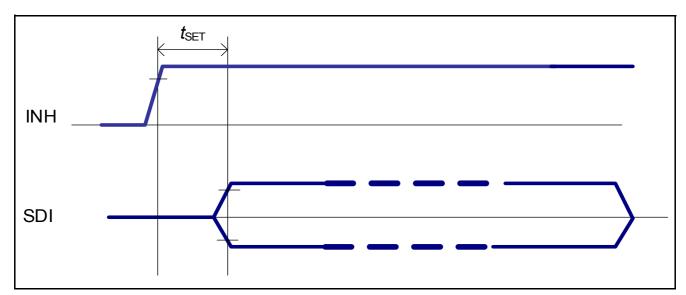


Figure 13 INH and SDI

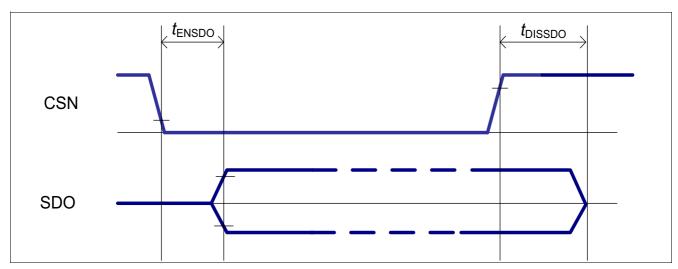


Figure 14 SPI SDO and CSN



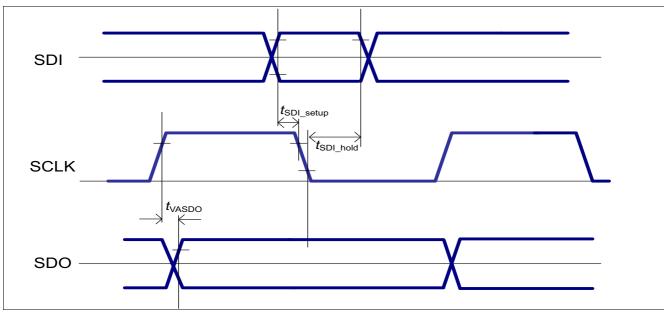


Figure 15 SPI SDI, SDO and SCLK

6.2 Status Register Reset

The SPI is using a standard shift-register concept with daisy-chain capability. Any data transmitted to the SPI will be available to the internal logic part at the end of the SPI transmission (CSN L -> H). To read a specific register, the address of the register is sent by the master to the SPI in a first SPI frame. The data that corresponds to this address is transmitted by the SDO during the following (second) SPI frame to the master. The default address for Status Register transmission after Power-ON Reset is 0.

The Status-Register-Reset command-bit is executed after the next SPI transmission. The two bits, Address Register and SRR act as command to read and reset (or not reset) the addressed Status-Register. The request and response behaviour of the SPI is further illustrated in **Figure 16** below.

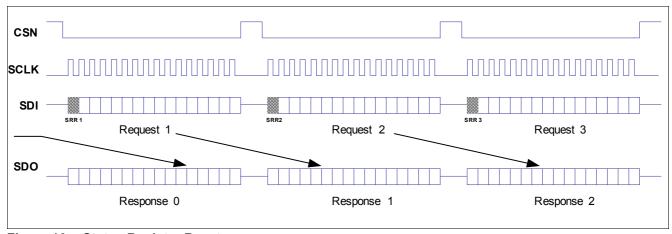


Figure 16 Status Register Reset



6.3 SPI Bit Definitions

6.3.1 Control - Word

Control Register Overview

Control Register 0 for HB 1: HB 6

| 15 | 14 | 13 | 12 | 11 | 10 | 9 | 8 | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|-----|----|--------------|-------------|-------------|-------------|-------------|-------------|-------------|--------------|--------------|--------------|--------------|--------------|--------------|---|
| SRR | 0 | OL_SD _EN | ACT_ HB6 | ACT_ HB5 | ACT_ HB4 | ACT_ HB3 | ACT_ HB2 | ACT_ HB1 | CONF_ HB6 | CONF_ HB5 | CONF_ HB4 | CONF_ HB3 | CONF_ HB2 | CONF_ HB1 | 0 |

Control Register 1 for HB 7 : HB 10

| 15 | 14 | 13 | 12 | 11 | 10 | 9 | 8 | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|-----|----|--------------|----|----|--------------|-------------|-------------|-------------|---|---|---------------|--------------|--------------|--------------|---|
| SRR | 1 | OL_SD _EN | x | x | ACT_ HB10 | ACT_ HB9 | ACT_ HB8 | ACT_ HB7 | x | x | CONF_ HB10 | CONF_ HB9 | CONF_ HB8 | CONF_ HB7 | 0 |

Table 3 Input (Control) Data Register

| Bit | Control Register - 0 HB 1:6 | Control Register - 1 HB 7:10 | Control Register - 0 HB 1:6 DESCRIPTION | Control Register - 1 HB 7:10 DESCRIPTION |
|--------|-----------------------------------|------------------------------------|--|---|
| Diagr | nosis & Regist | er Control | | |
| 15 | SRR (HB1:6) | SRR (HB7:10) | Status Register Reset (SRR) for HB1 to HB 6. If set to high, the errors bits of the coresponding status register are reset on the rising edge of CSN if sent to the uC. Low indicates no reset. | Status Register Reset (SRR) for HB7 to HB 10. If set to high, the errors bits of the coresponding status register are reset on the rising edge of CSN if sent to the uC. Low indicates no reset. |
| 14 | 0 | 1 | Address Register | |
| 13 | OL SD EN (HB1:6) | OL SD EN (HB7:10) | Open Load Detection Shutdown Enable (OL SD EN) for HB1 to HB 6. This feature allows the affected output stage to be switched off if a true open load or underload condition has been detected. It can be activated or deactivated by bit 13. | Open Load Detection Shutdown Enable (OL SD EN) for HB7 to HB 10. This feature allows the affected output stage to be switched off if a true open load or underload condition has been detected. It can be activated or deactivated by bit 13. |
| Activa | te Half-Bridge | X | | |
| 12 | ACT_HB 6 | X | H => Half Bridge 6 is active L => Half Bridge 6 is in Hi-Z | X => Don't Care |
| 11 | ACT_HB 5 | X | H => Half Bridge 5 is active L => Half Bridge 5 is in Hi-Z | X => Don't Care |
| 10 | ACT_HB 4 | ACT_HB 10 | H => Half Bridge 4 is active L => Half Bridge 4 is in Hi-Z | H => Half Bridge 10 is active L => Half Bridge 10 is in Hi-Z |

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Table 3 Input (Control) Data Register

| Bit | Control Register - 0 HB 1:6 | Control Register - 1 HB 7:10 | Control Register - 0 HB 1:6 DESCRIPTION | Control Register - 1 HB 7:10 DESCRIPTION |
|-------|-----------------------------------|------------------------------------|---|--|
| 9 | ACT_HB 3 | ACT_HB 9 | H => Half Bridge 3 is active L => Half Bridge 3 is in Hi-Z | H => Half Bridge 9 is active L => Half Bridge 9 is in Hi-Z |
| 8 | ACT_HB 2 | ACT_HB 8 | H => Half Bridge 2 is active L => Half Bridge 2 is in Hi-Z | H => Half Bridge 8 is active L => Half Bridge 8 is in Hi-Z |
| 7 | ACT_HB 1 | ACT_HB 7 | H => Half Bridge 1 is active L => Half Bridge 1 is in Hi-Z | H => Half Bridge 7 is active L => Half Bridge 7 is in Hi-Z |
| Confi | gure Half-Brid | ge X | | |
| 6 | CONF_HB 6 | X | H => HSD6 = ON & LSD6 = OFF L => HSD6 = OFF & LSD6 = ON | X => Don't Care |
| 5 | CONF_HB 5 | Х | H => HSD5 = ON & LSD5 = OFF L => HSD5 = OFF & LSD5 = ON | X => Don't Care |
| 4 | CONF_HB 4 | CONF_HB 10 | H => HSD4 = ON & LSD4 = OFF L => HSD4 = OFF & LSD4 = ON | H => HSD10 = ON & LSD10 = OFF L => HSD10 = OFF & LSD10 = ON |
| 3 | CONF_HB 3 | CONF_HB 9 | H => HSD3 = ON & LSD3 = OFF L => HSD3 = OFF & LSD3 = ON | H => HSD9 = ON & LSD9 = OFF L => HSD9 = OFF & LSD9 = ON |
| 2 | CONF_HB 2 | CONF_HB 8 | H => HSD2 = ON & LSD2 = OFF L => HSD2 = OFF & LSD2 = ON | H => HSD8 = ON & LSD8 = OFF L => HSD8 = OFF & LSD8 = ON |
| 1 | CONF_HB 1 | CONF_HB 7 | H => HSD1 = ON & LSD1 = OFF L => HSD1 = OFF & LSD1 = ON | H => HSD7 = ON & LSD7 = OFF L => HSD7 = OFF & LSD7 = ON |
| 0 | 0 | | Least Significant Bit (LSB) is set | to Low |



6.3.2 Diagnosis - Word

Diagnosis Register Overview

Diagnosis Register 0 for HB 1: HB 6

| 15 | 14 | 13 | 12 | 11 | 10 | 9 | 8 | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|----|-----|----|--------------|--------------|--------------|--------------|--------------|--------------|---------------|---------------|---------------|---------------|---------------|---------------|----|
| ос | PSF | OL | SACT_ HB6 | SACT_ HB5 | SACT_ HB4 | SACT_ HB3 | SACT_ HB2 | SACT_ HB1 | SCONF _HB6 | SCONF _HB5 | SCONF _HB4 | SCONF _HB3 | SCONF _HB2 | SCONF _HB1 | TW |

Diagnosis Register 1 for HB 7 : HB 10

| 15 | 14 | 13 | 12 | 11 | 10 | 9 | 8 | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 | |
|----|-----|----|----|----|---------------|--------------|--------------|--------------|---|---|----------------|---|---------------|---------------|----|--|
| ос | PSF | OL | x | x | SACT_ HB10 | SACT_ HB9 | SACT_ HB8 | SACT_ HB7 | x | x | SCONF _HB10 | | SCONF _HB8 | SCONF _HB7 | TW | |

Table 4 Output (Status) Data Register

| Bit | Status | Status | Status Register- 0 | Status Register - 1 | | | |
|-------|-----------------|--------------|--|--|--|--|--|
| | Register - 0 | Register - 1 | HB 1:6 | HB 7:10 | | | |
| | HB 1:6 | HB 7:10 | DESCRIPTION | DESCRIPTION | | | |
| Diag | nosis & Regist | er Control | | | | | |
| 15 | OC | ОС | Overcurrent Error is set if any one of | Overcurrent Error is set if any one of | | | |
| | (HB1:6) | (HB7:10) | HB1 to HB6 has an overload, short | HB7 to HB10 has an overload, short | | | |
| | | | circuit or cross current; The error is | circuit or cross current; The error is | | | |
| | | | latched and the corresponding output | latched and the corresponding | | | |
| | | | is switched off; | output is switched off; | | | |
| | | | Bit 15 error can only be reset via SRR | Bit 15 error can only be reset via | | | |
| | | | or power-on reset. | SRR or power-on reset. | | | |
| 14 | PSF | | Power Supply Failure; Global Error | Flag; | | | |
| | | | Bit 14 is set if VS has an overvoltag | e or undervoltage condition; | | | |
| | | | All outputs are switched OFF. | | | | |
| | | | Bit 14 is automatically reset if VS re | turns to its normal operating range. | | | |
| 13 | OL OL | | Open Load Error is set if any one of | Open Load Error is set if any one of | | | |
| | (HB1:6) | (HB7:10) | HB1 to HB6 has a true open load or | HB7 to HB10 has a true open load or | | | |
| | | | underload error condition; The error | underload error condition; The error | | | |
| | | | is latched. The corresponding output | is latched. The corresponding output | | | |
| | | | is switched off if Bit 13, OL SD EN of | is switched off if Bit 13, OL SD EN of | | | |
| | | | the Control Register is activated or | the Control Register is activated or | | | |
| | | | high. Bit 13 error can only be reset via | high. Bit 13 error can only be reset | | | |
| | | | SRR or power-on reset. | via SRR or power-on reset. | | | |
| Activ | ate Half-Bridge | X | | | | | |
| 12 | SACT_HB 6 | X | H => Half Bridge 6 is active | X => Don't Care | | | |
| | | | L => Half Bridge 6 is in Hi-Z | | | | |
| 11 | SACT_HB 5 | X | H => Half Bridge 5 is active | X => Don't Care | | | |
| | _ | | L => Half Bridge 5 is in Hi-Z | | | | |
| | | | 2 Trail Bridge 6 15 III Til 2 | | | | |



Table 4 Output (Status) Data Register

| Bit | Status Register - 0 HB 1:6 | Status Register - 1 HB 7:10 | Status Register- 0 HB 1:6 DESCRIPTION | Status Register - 1 HB 7:10 DESCRIPTION |
|------|----------------------------------|-----------------------------------|---|--|
| 10 | SACT_HB 4 | SACT_HB 10 | H => Half Bridge 4 is active L => Half Bridge 4 is in Hi-Z | H => Half Bridge 10 is active L => Half Bridge 10 is in Hi-Z |
| 9 | SACT_HB 3 | SACT_HB 9 | H => Half Bridge 3 is active L => Half Bridge 3 is in Hi-Z | H => Half Bridge 9 is active L => Half Bridge 9 is in Hi-Z |
| 8 | SACT_HB 2 | SACT_HB 8 | H => Half Bridge 2 is active L => Half Bridge 2 is in Hi-Z | H => Half Bridge 8 is active L => Half Bridge 8 is in Hi-Z |
| 7 | SACT_HB 1 | SACT_HB 7 | H => Half Bridge 1 is active L => Half Bridge 1 is in Hi-Z | H => Half Bridge 7 is active L => Half Bridge 7 is in Hi-Z |
| Conf | igure Half-Bridç | ge X | | |
| 6 | SCONF_HB 6 | X | H => HSD6 = ON & LSD6 = OFF L => HSD6 = OFF & LSD6 = ON | X => Don't Care |
| 5 | SCONF_HB 5 | Х | H => HSD5 = ON & LSD5 = OFF L => HSD5 = OFF & LSD5 = ON | X => Don't Care |
| 4 | SCONF_HB 4 | SCONF_HB 10 | H => HSD4 = ON & LSD4 = OFF L => HSD4 = OFF & LSD4 = ON | H => HSD10 = ON & LSD10 = OFF L => HSD10 = OFF & LSD10 = ON |
| 3 | SCONF_HB | SCONF_HB 9 | H => HSD3 = ON & LSD3 = OFF L => HSD3 = OFF & LSD3 = ON | H => HSD9 = ON & LSD9 = OFF L => HSD9 = OFF & LSD9 = ON |
| 2 | SCONF_HB 2 | SCONF_HB 8 | H => HSD2 = ON & LSD2 = OFF L => HSD2 = OFF & LSD2 = ON | H => HSD8 = ON & LSD8 = OFF L => HSD8 = OFF & LSD8 = ON |
| 1 | SCONF_HB 1 | SCONF_HB 7 | H => HSD1 = ON & LSD1 = OFF L => HSD1 = OFF & LSD1 = ON | H => HSD7 = ON & LSD7 = OFF L => HSD7 = OFF & LSD7 = ON |
| 0 | TW | ı | _ | g and will be set to High if the junction remains on until one or more sensors a switched off simultaneously. Bit 0 is |

Note: Status HBx represents status of Half-Bridge Driver and NOT status of Control Register.

Note: The PSF and TW bits in the first Diagnosis word will reflect the current clock cycle status, all other remaining bits are 0.



Application Information

7 Application Information

Note: The following simplified application examples are given as a hint for the implementation of the device only and shall not be regarded as a description or warranty of a certain functionality, condition or quality of the device. The function of the described circuits must be verified in the real application.

7.1 Application Diagram

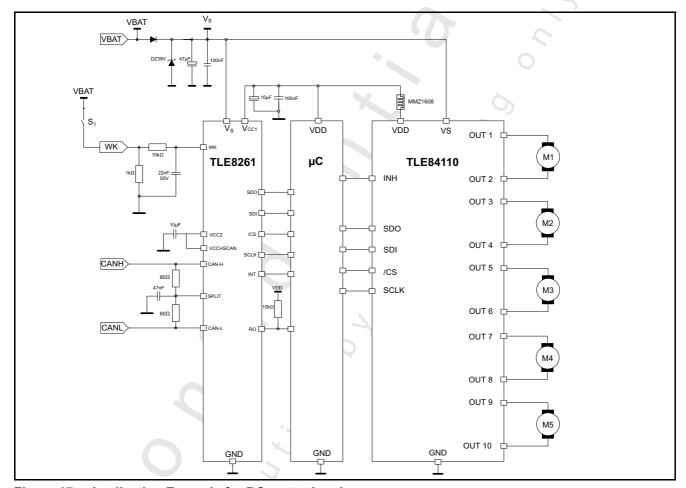


Figure 17 Application Example for DC-motor Loads

For optimum EMC performance, a ferrite is recommended to be placed in series and as close as possible to the Vdd line of the TLE841xy device. This is shown in the above application diagram example. The ferrite should have an impedance of 1000ohm at an effective frequency of 100MHz frequency. A recommended ferrite is the MMZ1608 type series available in a geometry size of 0603 with a DC resistance of 0.60hm and allowable DC current of 190mA.

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Application Information

7.2 Thermal application information

Ta = -40°C, Ch 1 to Ch 10 are dissipating a total of 2.5W (0.25W each). Ta = 85°C, Ch 1 to Ch 10 are dissipating a total of 1.8W (0.18W each).

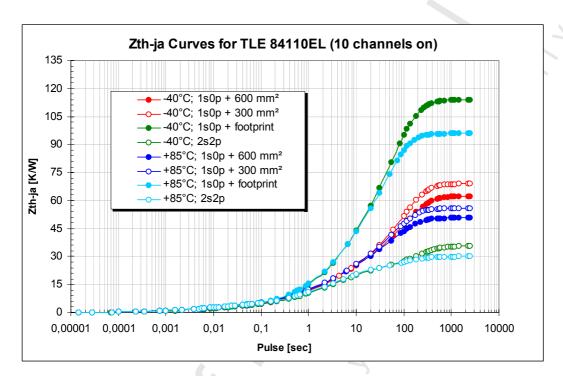


Figure 18 ZthJA Curve for different PCB setups

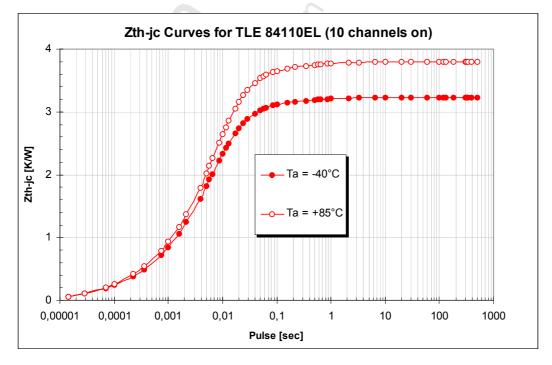


Figure 19 ZthJC Curve



Application Information

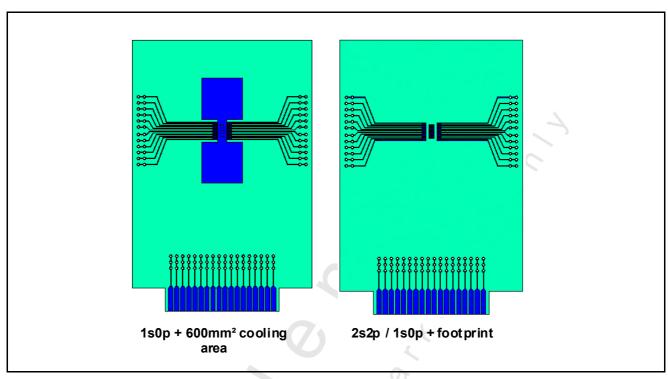


Figure 20 Board Setup

Board Setup based on JESD 51-3, -7 FR4 PCB with 35µm Cu.



Package Outlines

8 Package Outlines

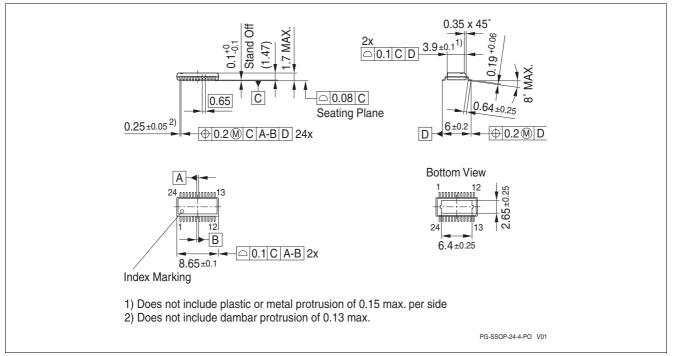


Figure 21 PG-SSOP-24-4 (Plastic/Plastic Green - Dual Small Outline Package)

Green Product (RoHS compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).



Revision History

9 Revision History

0.30.40

TLE84110EL

Revision History: Rev. 1.0, 2010-04-27

| Version | Subjects (major changes since last revision) |
|---------|--|
| | |
| 1.0 | Final Data Sheet Release |

Data Sheet 32 Rev. 1.0, 2010-04-27

Edition 2010-04-27

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For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.